

SANYO

No.1973A

2SA1469/2SC3746

PNP/NPN Epitaxial Planar Silicon Transistors

60V/5A High-Speed Switching Applications**Applications**

- Various inductance lamp drivers for electrical equipment.
- Inverters, converters (strobo, flash, fluorescent lamp lighting circuit).
- Power amp (high power car stereo, motor controller).
- High-speed switching (switching regulator, driver).

Features

- Low saturation voltage.
- Excellent current dependence of h_{FE} .
- Short switching time.
- Micaless package facilitating mounting.

() : 2SA1469

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CBO}	(-)80	V
Collector-to-Emitter Voltage	V_{CEO}	(-)60	V
Emitter-to-Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)5	A
Collector Current (Pulse)	I_{CP}	(-)7	A
Collector Dissipation	P_C	2	W
		20	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	- 55 to + 150	$^\circ\text{C}$

 $T_c = 25^\circ\text{C}$ **Electrical Characteristics at $T_a = 25^\circ\text{C}$**

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)40\text{V}, I_E = 0$			(-)0.1	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4\text{V}, I_C = 0$			(-)0.1	mA
DC Current Gain	h_{FE}	$V_{CE} = (-)2\text{V}, I_C = (-)1\text{A}$	70*		280*	
Gain-Bandwidth Product	f_T	$V_{CE} = (-)5\text{V}, I_C = (-)1\text{A}$		100		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)2.5\text{A}, I_B = (-)0.125\text{A}$			(-)0.4	V

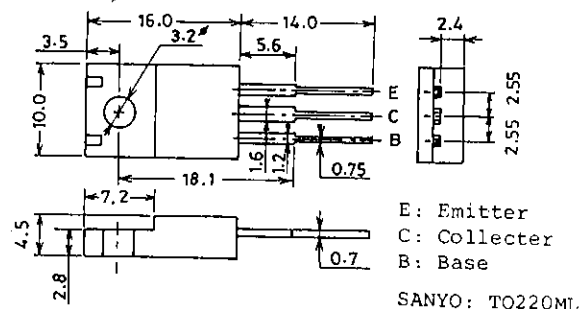
Continued on next page.

* : The 2SA1469/2SC3746 are classified by 1A h_{FE} as follows

70	Q	140	100	R	200	140	S	280
----	---	-----	-----	---	-----	-----	---	-----

Package Dimensions 2041

(unit : mm)

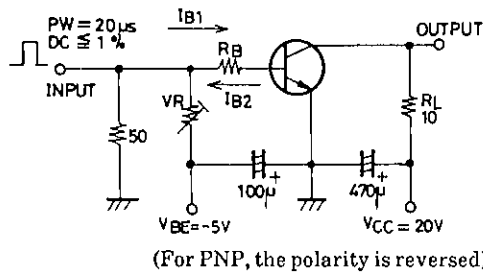


SANYO Electric Co., Ltd. Semiconductor Business Headquarters
 TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

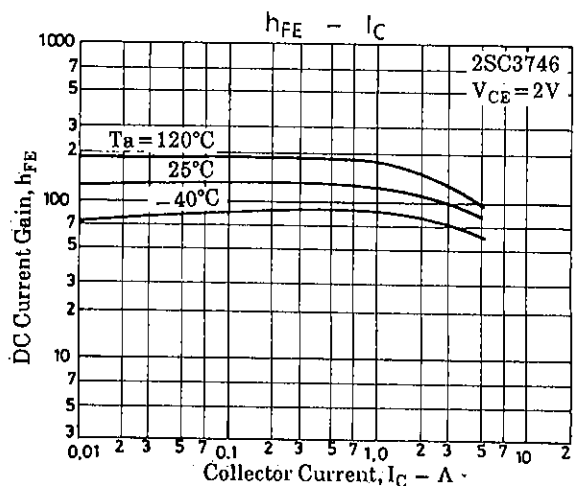
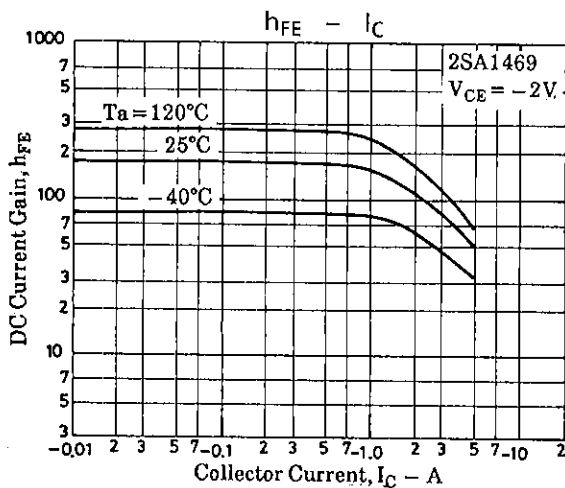
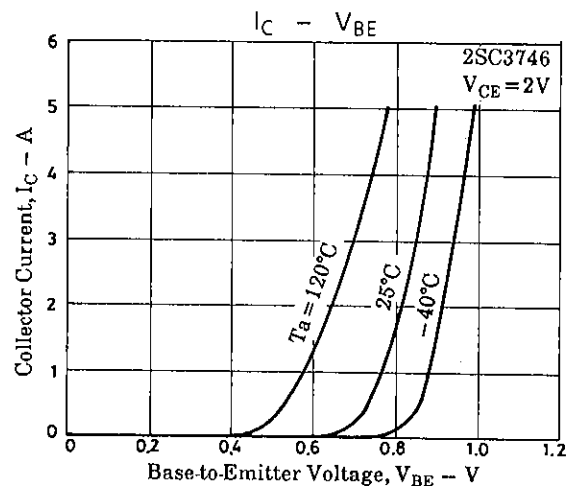
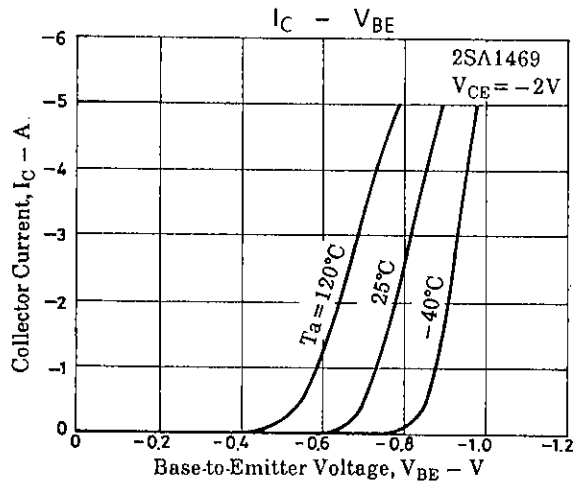
Continued from preceding page.

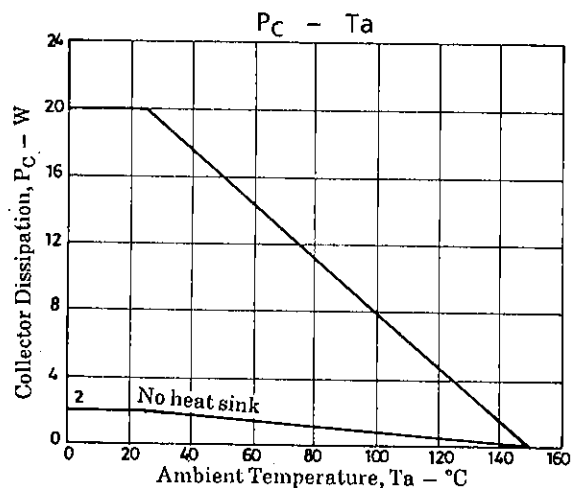
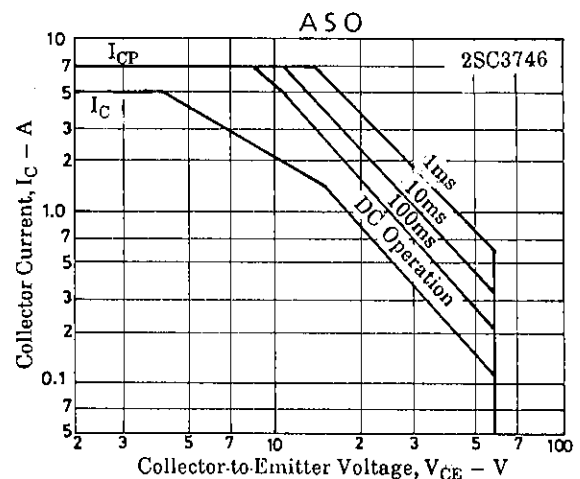
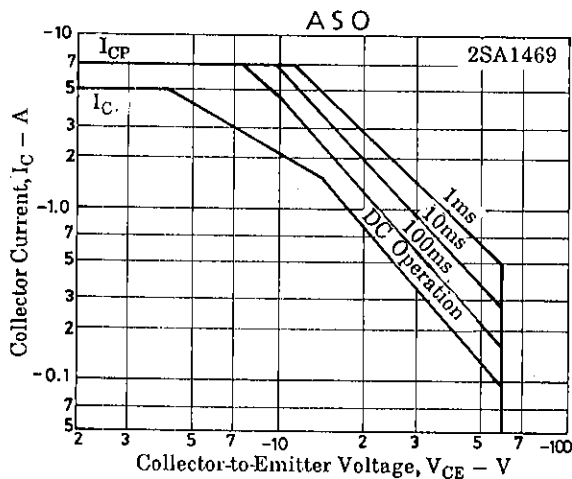
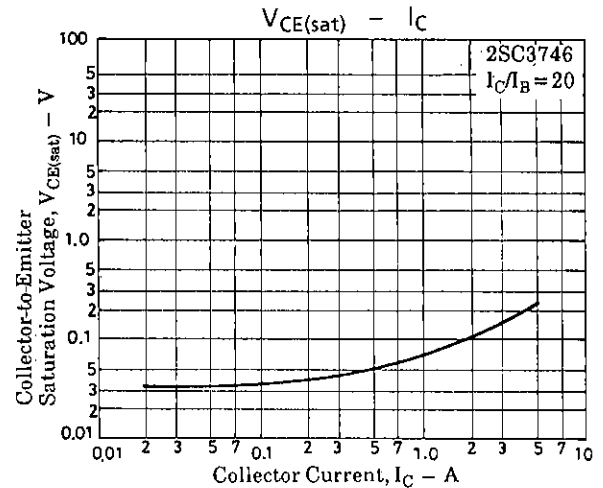
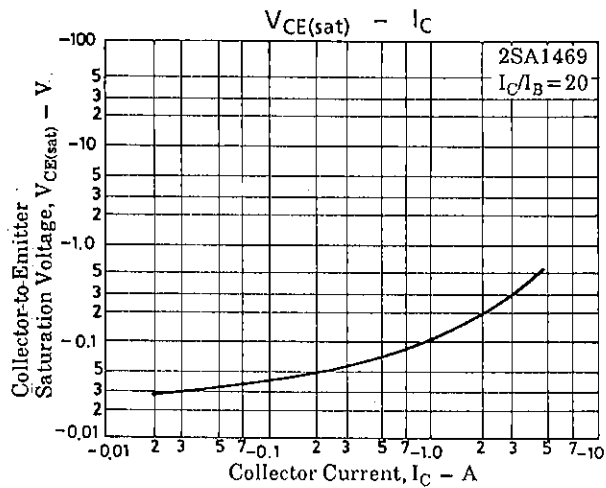
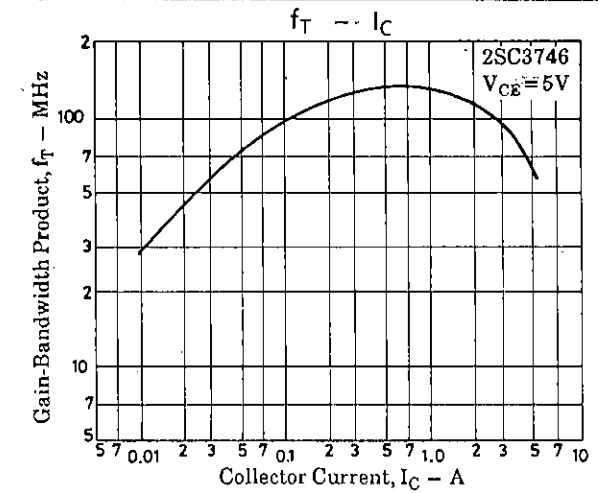
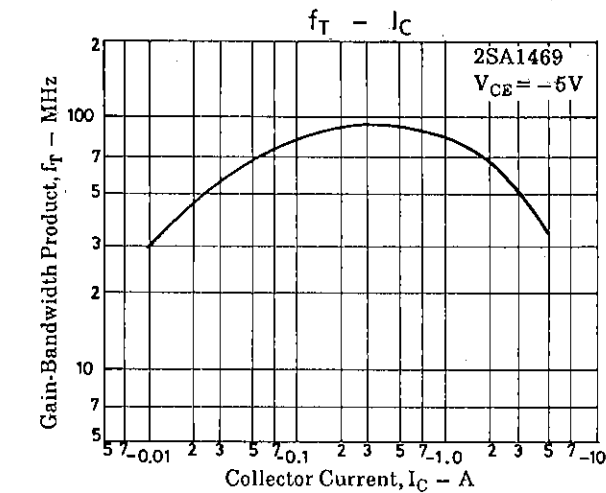
			min	typ	max	unit
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)1\text{mA}, I_E = 0$	$(-)80$			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1\text{mA}, R_{BE} = \infty$	$(-)60$			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)1\text{mA}, I_C = 0$	$(-)5$			V
Turn-on Time	t_{on}	See specified Test Circuit.		0.1		μs
Storage Time	t_{stg}	"		0.5		μs
Fall Time	t_f	"		0.1		μs

Switching Time Test Circuit



$$20I_{B1} = -20I_{B2} = I_C = 2\text{A}$$

Unit (Resistance : Ω , Capacitance : F)



- No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.
- Anyone purchasing any products described or contained herein for an above-mentioned use shall:
 - ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use;
 - ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.